

SEMICONDUCTOR

TECHNICAL DATA

FTK2306

DESCRIPTION

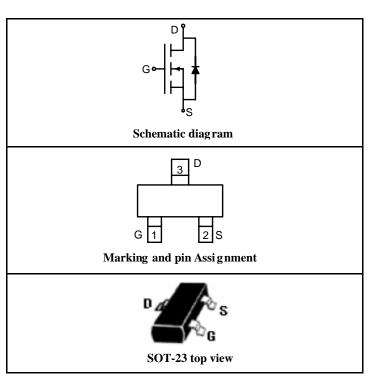
The FTK2306 uses advanced trench technology to provide excellent $R_{\text{DS(ON)}}$, low gate charge and operation with gate voltages as low as 2.5V.

GENERAL FEATURES

- $V_{DS} = 30V, I_D = 5A$ $R_{DS(ON)} < 50mΩ$ @ $V_{GS} = 2.5V$ $R_{DS(ON)} < 35mΩ$ @ $V_{GS} = 4.5V$
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Application

- Battery protection
- Load switch
- Power management



PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2306 or RO	FTK2306	SOT23-3	Ø180mm	8 mm	3000 units

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	Vgs	±12	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I _D	5	Α
Diain Current-Continuous@ Current-Pulsed (Note 1)	I _{DM}	20	Α
Maximum Power Dissipation	P _D	1.38	W
Operating Junction and Storage Temperature Range	T_J,T_STG	-55 To 150	$^{\circ}\mathbb{C}$
THERMAL CHARACTERISTICS			
Thermal Resistance, Junction-to-Ambient (Note 2)	R _{θJA}	90	°C/W

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V			1	μΑ
Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$			±100	nA
ON CHARACTERISTICS (Note 3)			•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.5		1.2	V
		V _{GS} =2.5V, I _D =2.6A			50	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =5A			35	mΩ
		V_{GS} =10V, I_D =5A			30	mΩ
Forward Transconductance	G FS	$V_{DS}=5V,I_{D}=5A$		13		S



DYNAMIC CHARACTERISTICS (Note4)					
Input Capacitance	C _{Iss}		660	1050	PF
Output Capacitance	Coss	V_{DS} =25V, V_{GS} =0V, F=1.0MHz	90		PF
Reverse Transfer Capacitance	C _{rss}		70		PF
SWITCHING CHARACTERISTICS (Note 4)					
Turn-on Delay Time	t _{d(on)}		6		nS
Turn-on Rise Time	t _r	$V_{DS}=15V,I_{D}=5A$ $V_{GS}=10V,R_{GEN}=3.3\Omega$	20		nS
Turn-Off Delay Time	t _{d(off)}	$R_{D}=3\Omega$	20		nS
Turn-Off Fall Time	t _f		3		nS
Total Gate Charge	Qg		8.5	15	nC
Gate-Source Charge	Q_{gs}	V _{DS} =16V,I _D =5A,V _{GS} =4.5V	1.5		nC
Gate-Drain Charge	Q_{gd}		3.2	_	nC
DRAIN-SOURCE DIODE CHARACTERISTICS					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =1.2A		1.2	V

NOTES:

- Repetitive Rating: Pulse width limited by maximum junction temperature.
 Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

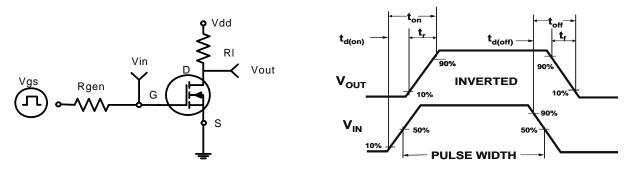
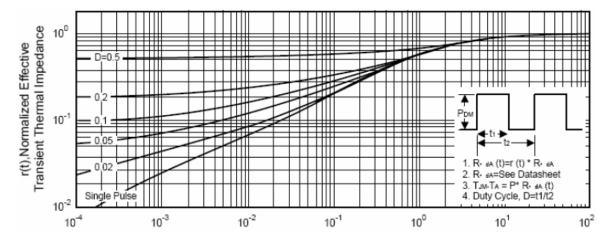


Figure 1: Switching Test Circuit

Figure 2:Switching Waveforms



Square Wave Pluse Duration(sec) Figure 3: Normalized Maximum Transient Thermal Impedance



TYPICAL ELECTRICAL CHARACTERISTICS

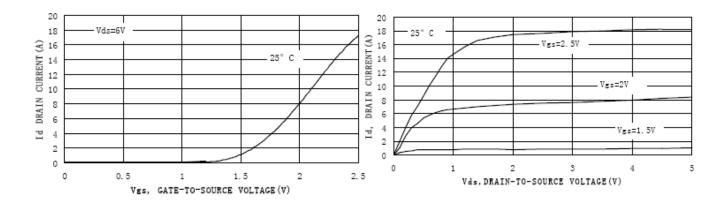


Figure 1. Transfer Characteristics

Figure 2. On-Region Characteristics

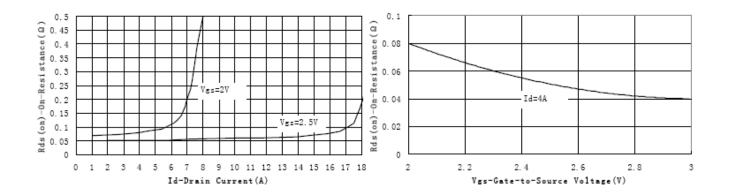
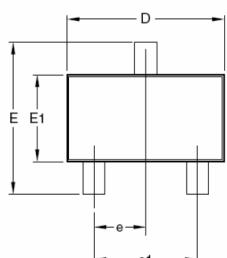


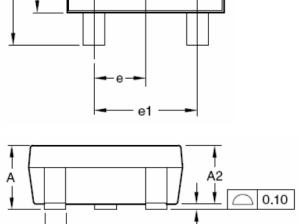
Figure 3. On-Resistance versus Drain Current

Figure 4. On-Resistance vs. Gate-to-Source Voltage



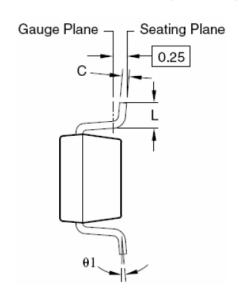
SOT-23 PACKAGE INFORMATION



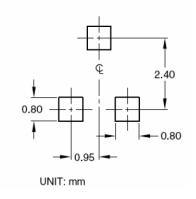


Α1

Dimensions in Millimeters (UNIT:mm)



RECOMMENDED LAND PATTERN



Dimensions in millimeters

Symbols	Min.	Nom.	Max.		
Α	0.90	-	1.25		
A1	0.00	-	0.13		
A2	0.70	1.00	1.15		
b	0.30	0.40	0.50		
С	0.08	0.13	0.20		
D	2.80	2.90	3.10		
E	2.60	2.80	3.00		
Et	1.40	1.60	1.80		
e	0.95 BSC				
e1	1.90 BSC				
L	0.30	-	0.60		
01	0 °	5°	8°		

Dimensions in inches

Symbols	Min.	Nom.	Max.		
Α	0.035	her en	0.049		
A1	0.000	lip a-t ar	0.005		
A2	0.028	0.039	0.045		
ь	0.012	0.016	0.020		
C	0.003	0.005	0.008		
D	0.110	0.114	0.122		
E	0.102	0.110	0.118		
E1	0.055	0.063	0.071		
е	0	.037 BS	C		
e1	0.075 BSC				
LL	0.012		0.024		
01	00	5°	80		

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NOTES:

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified

Revision No: 2

- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.